

# INSTITUTE OF AERONAUTICAL ENGINEERING

(Autonomous)

Dundigal, Hyderabad - 500 043

## ELECTRICAL AND ELECTRONICS ENGINEERING

## ATTAINMENT OF COURSE OUTCOME - ACTION TAKEN REPORT

Name of the faculty:	S Rambabu	Department:	EEE	
Regulation:	IARE - R16	Batch:	2016 - 2020	
Course Name:	Electronic Devices and Circuits	Course Code:	AEC001	
Semester:	III	Target Value:	60% (1.8)	

## Attainment of COs:

	Course Outcome	Direct attainment	Indirect attainment	Overall attainment	Observation
CO1	Illustrate the characteristics of semiconductor devices for determining the device parameters such as resistances, current gain and voltage gain.	2.7	2.4	2.6	Attained
CO2	Apply the pn junction characteristics for the diode applications such as switch and rectifiers.	2	2.4	2.1	Attained
CO3	Examine DC and AC load line analysis of BJT and FET amplifiers for optimal operating level regardless of input, load placed on the device.	1.3	2.4	1.5	Not Attained
CO4	Extend the biasing techniques for bipolar and uni-polar transistor for establishing a proper operating point.	1.7	2.4	1.8	Attained
CO5	Utilize low frequency model for estimation of the characteristic parameters of BJT, FET amplifier circuits.	1.3	2.3	1.5	Not Attained
CO6	Demonstrate the working principle of special purpose semiconductor diodes and transistors for triggering and voltage regulation applications.	1.3	2.4	1.5	Not Attained

#### Action taken report:

CO 3: Need to focus on bipolar junction transistors, Field effect transistors

CO 5: Provide more assignments on characteristic parameters of BJT, FET amplifier circuits.

CO 6: Provide more focus on special purpose semiconductor diodes

**Course Coordinator** 

Mentor

Head of the December of the Electrical and Electric